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# PM50150K

Silicon N-Channel Power MOS FET Module

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## Application

High Speed Power Switching

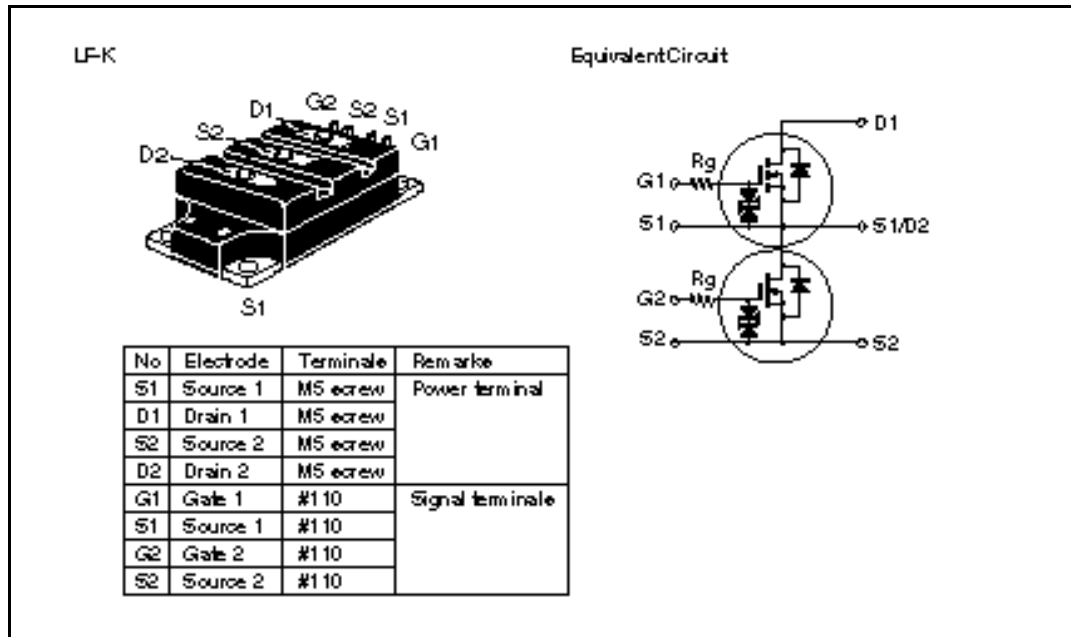
## Features

- Equipped with Power MOS FET
- Low on-resistance
- High speed switching
- Low drive current
- Wide area of safe operation
- Inherent parallel diode between source and drain
- Isolated base from Terminal
- Suitable for motor driver, switching regulator and etc.



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### Outline



### Absolute Maximum Ratings (Ta = 25°C) (Per FET chip)

Item	Symbol	Rating	Unit
Drain source voltage	$V_{(BR)DSS}$	500	V
Gate source voltage	$V_{(BR)GSS}$	±30	V
Drain current	$I_D$	150	A
Drain peak current	$I_{D(peak)}$	360	A
Body to drain diode reverse drain current	$I_{DR}$	150	A
Body to drain diode reverse peak current	$I_{DR(peak)}$	360	A
Channel dissipation	$P_{ch}^{*1}$	500	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	−45 to +125	°C
Insulation dielectric	$V_{iso}^{*2}$	2000	Vrms

Notes: 1. Value at Ta = 25°C

2. Base to terminals AC minute

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**Electrical Characteristics** (Ta = 25°C) (Per FET chip)

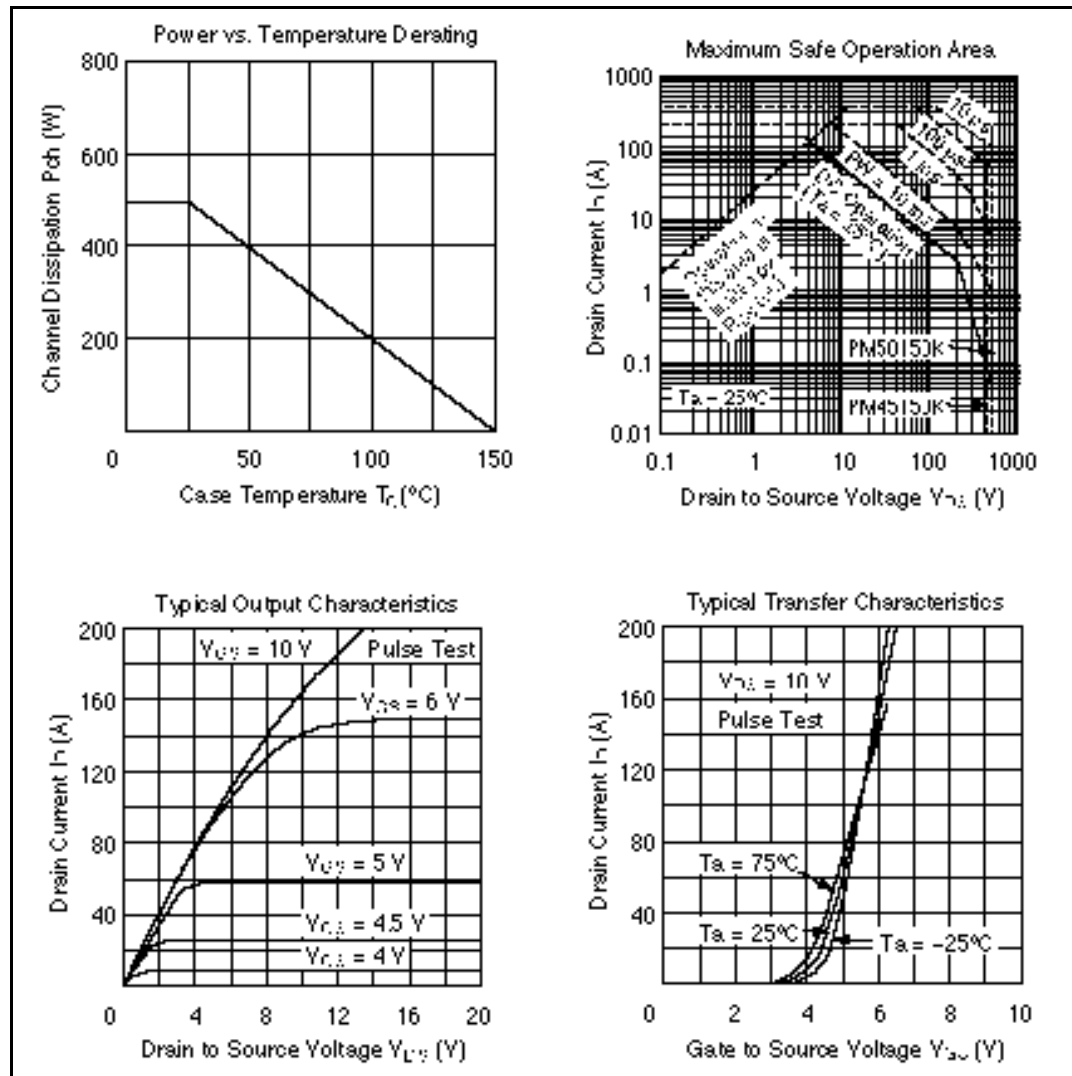
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0 \text{ V}$
Gate to source leak current	$I_{GSS}$	—	—	±10	μA	$V_{GS} = \pm 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	—	—	V	$I_G = \pm 100 \text{ μA}$ , $V_{DS} = 0 \text{ V}$
Drain leak current	$I_{DSS}$	—	—	1	mA	$V_{DS} = 400 \text{ V}$ , $V_{GS} = 0 \text{ V}$
Gate to source threshold voltage	$V_{GS(th)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$ , $V_{DS} = 10 \text{ V}$
Drain to source saturation voltage	$V_{DS(on)}$	—	4.5	6.0	V	$I_D = 75 \text{ A}$ , $V_{GS} = 10 \text{ V}^{*1}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.06	0.08		$I_D = 75 \text{ A}$ , $V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	—	80	—	S	$I_D = 75 \text{ A}$ , $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	$C_{iss}$	—	22600	—	pF	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0 \text{ V}$
Output capacitance	$C_{oss}$	—	4600	—		$f = 1 \text{ MHz}$
Reverse transfer capacitance	$C_{rss}$	—	580	—		
Turn-on delay time	$t_{d(on)}$	—	280	—	ns	$I_D = 75 \text{ A}$ , $V_{GS} = 10 \text{ V}$
Rise time	$t_r$	—	820	—		$R_g = 50$
Turn-off delay time	$t_{d(off)}$	—	1190	—		$R_L = 0.4$
Fall time	$t_f$	—	400	—		
Body to drain diode forward voltage	$V_{DF}$	—	2.0	—	V	$I_F = 150 \text{ A}$ , $V_{GS} = 0 \text{ V}$
Body to drain diode reverse recovery time	$t_{rr}$	—	140	—	ns	$I_F = 150 \text{ A}$ , $V_{GS} = 0 \text{ V}$ $di/dt = 100 \text{ A/μs}$

Note: 1. Pulse Test

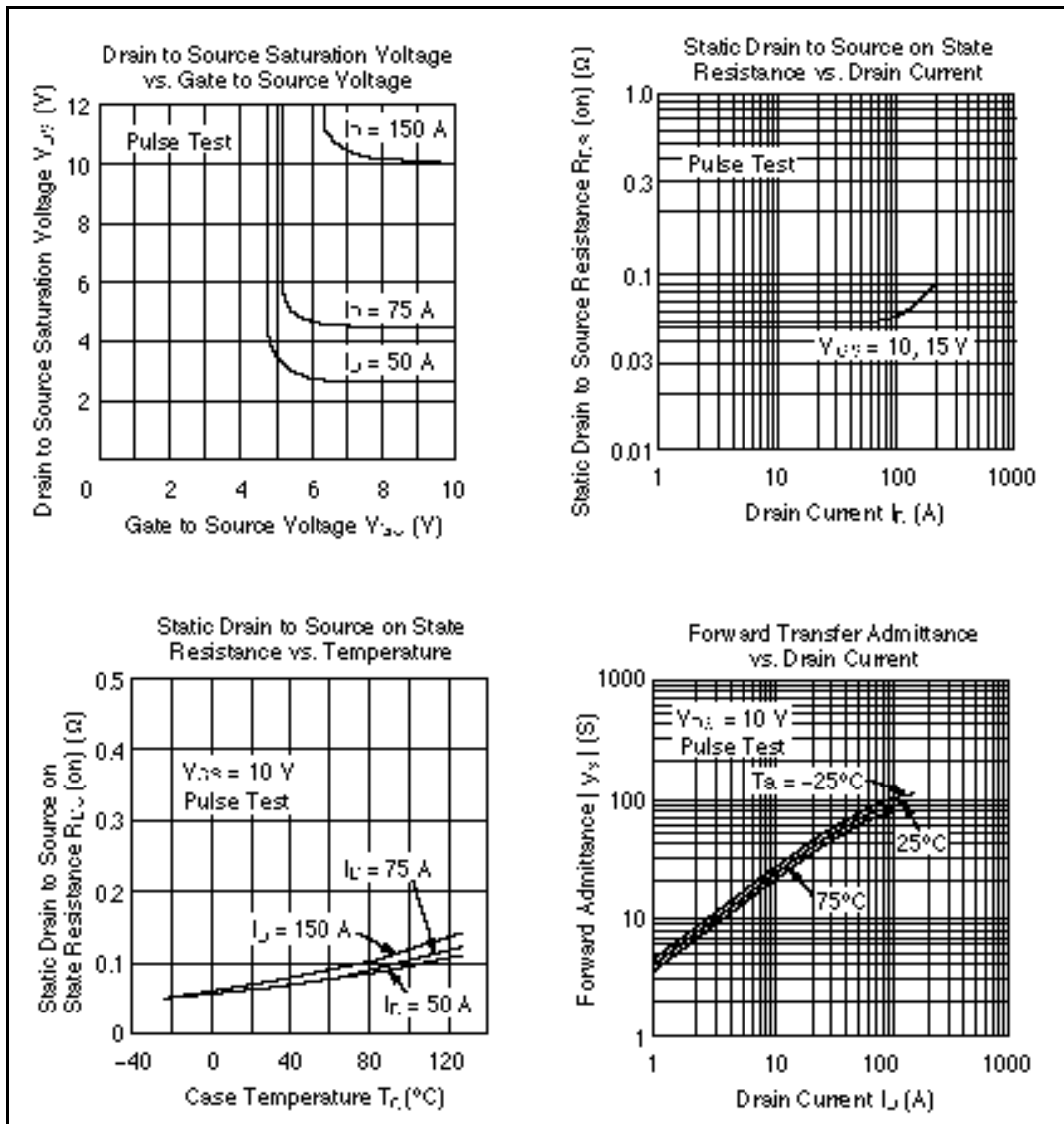
**Mechanical Characteristics**

Item	Symbol	Condition	Rating	Unit
Fixing strength	—	Mounting into main-terminal with M4 screw	1.45 to 1.95	N-m
	—	Mounting into heat sink with M5 screw	1.95 to 2.9	N-m
Weight	—	Typical value	380	g

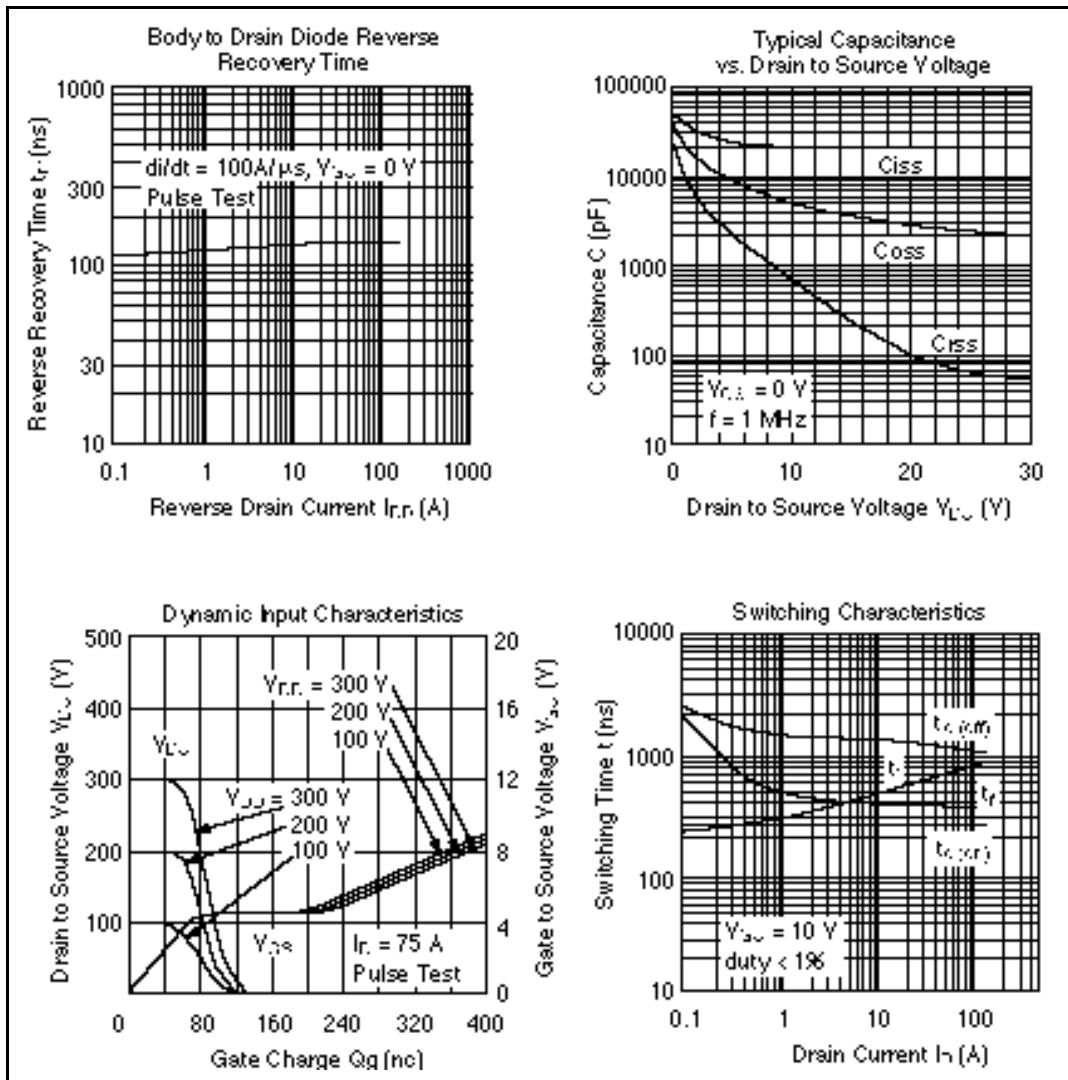
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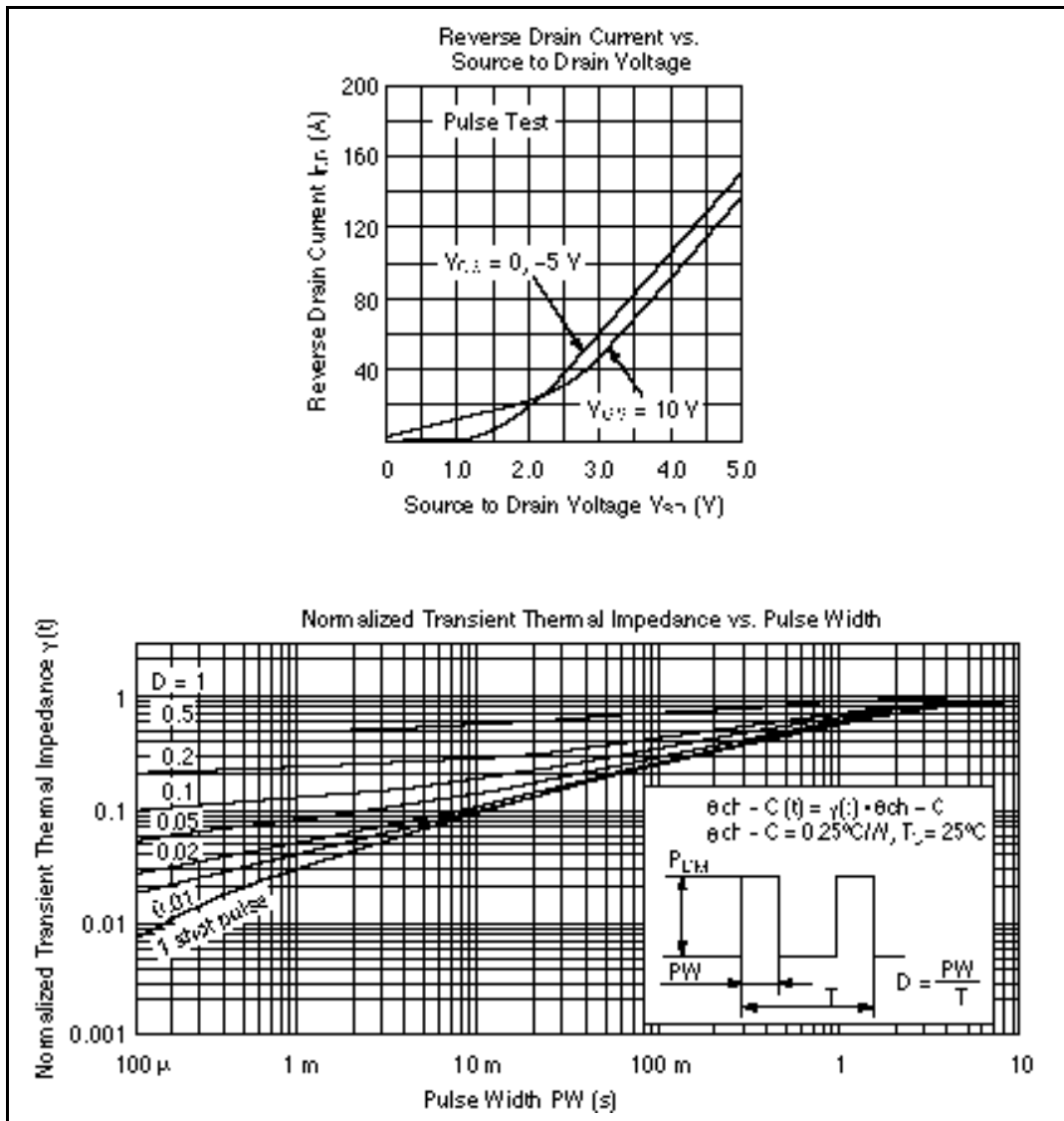
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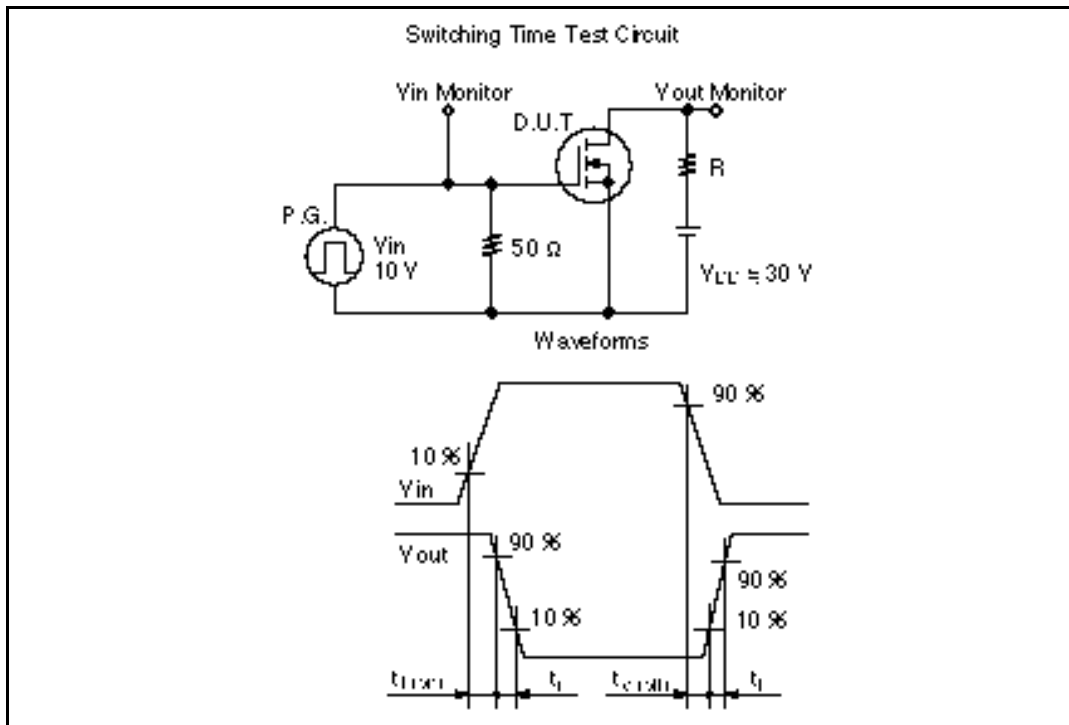
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## Hitachi, Ltd.

Semiconductor & IC Div.  
Nippon Bldg., 2-5-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan  
Tel Tokyo (03) 3270-2111  
Fax: (03) 3270-5109

### For further information write to:

Hitachi America, Ltd.  
Semiconductor & IC Div.  
2000 Sierra Point Parkway  
Briarcliff, CA. 94005-1835  
U.S.A.  
Tel 415-589-8300  
Fax 415-589-4207

Hitachi Europe GmbH  
Electronic Components Group  
Continental Europe  
Dornacher Straße 3  
D-85622 Feldkirchen  
München  
Tel 089-9 24 80-0  
Fax 089-9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Div.  
Northern Europe Headquarters  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA  
United Kingdom  
Tel 0628-585000  
Fax 0628-778322

Hitachi Asia Pte. Ltd.  
45 Collyer Quay #20-00  
Hitachi Tower  
Singapore 0404  
Tel 535-2400  
Fax 535-1533

Hitachi Asia (Hong Kong) Ltd.  
Unit 705, North Tower,  
World Finance Centre  
Harbour City, Canton Road  
Tsim Sha Tsui, Kowloon  
Hong Kong  
Tel 27359218  
Fax 27308074